# Octal 3-State Noninverting Buffer/Line Driver/Line Receiver

### **High-Performance Silicon-Gate CMOS**

The MC74HC541A is identical in pinout to the LS541. The device inputs are compatible with Standard CMOS outputs. External pull–up resistors make them compatible with LSTTL outputs.

The HC541A is an octal noninverting buffer/line driver/line receiver designed to be used with 3-state memory address drivers, clock drivers, and other bus-oriented systems. This device features inputs and outputs on opposite sides of the package and two ANDed active-low output enables.

The HC541A is similar in function to the HC540A, which has inverting outputs.

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 2 to 6V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance With the JEDEC Standard No. 7A Requirements
- Chip Complexity: 134 FETs or 33.5 Equivalent Gates

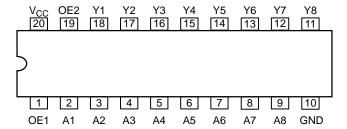


Figure 1. Pinout: 20-Lead Packages (Top View)

### **FUNCTION TABLE**

	Inputs	Output V	
OE1	OE2	Α	Output Y
L	L	L	L
L	L	Н	Н
Н	X	Х	Z
X	Н	Х	Z

X = Don't Care Z = High Impedance



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MARKING DIAGRAMS



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PDIP-20 N SUFFIX CASE 783

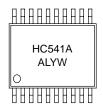


SO-20 DW SUFFIX CASE 751D





TSSOP-20 DT SUFFIX CASE 948E



A = Assembly Location

L, WL = Wafer Lot Y, YY = Year W, WW = Work Week

### ORDERING INFORMATION

Device	Package	Shipping
MC74HC541AN	PDIP-20	1440/Box
MC74HC541ADW	SOIC-WIDE	38/Rail
MC74HC541ADWR2	SOIC-WIDE	1000/Reel
MC74HC541ADT	TSSOP-20	75/Rail
MC74HC541ADTR2	TSSOP-20	2500/Reel

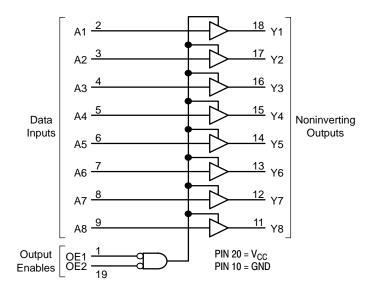


Figure 2. Logic Diagram

### **MAXIMUM RATINGS** (Note 1)

Symbol	F	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage		-0.5  to  +7.0	V
VI	DC Input Voltage		$-0.5 \le V_{  } \le +0.5$	V
V <sub>O</sub>	DC Output Voltage	(Note 2)	$-0.5 \le V_{O} \le +0.5$	V
I <sub>IK</sub>	DC Input Diode Current		±20	mA
I <sub>OK</sub>	DC Output Diode Current		±35	mA
I <sub>O</sub>	DC Output Sink Current		±35	mA
I <sub>CC</sub>	DC Supply Current per Supply Pin		±75	mA
I <sub>GND</sub>	DC Ground Current per Ground Pin		±75	mA
T <sub>STG</sub>	Storage Temperature Range		-65 to +150	°C
TL	Lead Temperature, 1 mm from Case	for 10 Seconds	260	°C
TJ	Junction Temperature under Bias		+150	°C
$\theta_{\sf JA}$	Thermal Resistance	PDIP SOIC TSSOP	67 96 128	°C/W
P <sub>D</sub>	Power Dissipation in Still Air at 85°C	PDIP SOIC TSSOP	750 500 450	mW
MSL	Moisture Sensitivity		Level 1	
F <sub>R</sub>	Flammability Rating	Oxygen Index: 30% – 35%	UL-94-VO (0.125 in)	
V <sub>ESD</sub>	ESD Withstand Voltage	Human Body Model (Note 3) Machine Model (Note 4) Charged Device Model (Note 5)	> 4000 > 300 > 1000	V
I <sub>Latch-Up</sub>	Latch–Up Performance	Above V <sub>CC</sub> and Below GND at 85°C (Note 6)	±300	mA

<sup>1.</sup> Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Extended exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute maximum—rated conditions is not implied.

- 2. I<sub>O</sub> absolute maximum rating must be observed.
- 3. Tested to EIA/JESD22–A114–A.
- 4. Tested to EIA/JESD22-A115-A.
- 5. Tested to JESD22-C101-A.
- 6. Tested to EIA/JESD78.
- 7. For high frequency or heavy load considerations, see the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

### RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter			Max	Unit
V <sub>CC</sub>	DC Supply Voltage	(Referenced to GND)	2.0	6.0	V
V <sub>IN</sub> , V <sub>OUT</sub>	DC Input Voltage, Output Voltage	(Referenced to GND)	0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature Range, All Package Types		-55	+ 125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise/Fall Time (Figure 3)	$V_{CC} = 2.0 \text{ V}$ $V_{CC} = 4.5 \text{ V}$ $V_{CC} = 6.0 \text{ V}$	0 0 0	1000 500 400	ns

8. Unused inputs may not be left open. All inputs must be tied to a high-logic voltage level or a low-logic input voltage level.

### **DC CHARACTERISTICS** (Voltages Referenced to GND)

			V <sub>CC</sub>	Guaranteed Limit		t	
Symbol	Parameter	Condition	V	−55°C to 25°C	≤85°C	≤125°C	Unit
V <sub>IH</sub>	Minimum High–Level Input Voltage	V <sub>OUT</sub> = 0.1 V  I <sub>OUT</sub>   ≤ 20 μA	2.0 3.0	1.50 2.10	1.50 2.10	1.50 2.10	V
	Voltage	1001  = 20 μΛ	3.0 4.5	3.15	3.15	3.15	
			6.0	4.20	4.20	4.20	
V <sub>IL</sub>	Maximum Low-Level Input	$V_{OUT} = V_{CC} - 0.1 \text{ V}$	2.0	0.50	0.50	0.50	V
	Voltage	I <sub>OUT</sub>   ≤ 20 μA	3.0	0.90	0.90	0.90	
			4.5	1.35	1.35	1.35	
			6.0	1.80	1.80	1.80	
$V_{OH}$	Minimum High-Level Output	$V_{IN} = V_{IL}$	2.0	1.9	1.9	1.9	V
	Voltage	I <sub>OUT</sub>   ≤ 20 μA	4.5	4.4	4.4	4.4	
			6.0	5.9	5.9	5.9	
		$V_{IN} = V_{IL}$ $ I_{OUT}  \le 3.6 \text{ mA}$	3.0	2.48	2.34	2.20	
		I <sub>OUT</sub>   ≤ 6.0 mA	4.5	3.98	3.84	3.70	
		I <sub>OUT</sub>   ≤ 7.8 mA	6.0	5.48	5.34	5.20	
V <sub>OL</sub>	Maximum Low-Level Output	$V_{IN} = V_{IH}$	2.0	0.1	0.1	0.1	V
	Voltage	I <sub>OUT</sub>   ≤ 20 μA	4.5	0.1	0.1	0.1	
			6.0	0.1	0.1	0.1	
		$V_{IN} = V_{IH}$ $ I_{OUT}  \le 3.6 \text{ mA}$	3.0	0.26	0.33	0.40	
		I <sub>OUT</sub>   ≤ 6.0 mA	4.5	0.26	0.33	0.40	
		I <sub>OUT</sub>   ≤ 7.8 mA	6.0	0.26	0.33	0.40	
I <sub>IN</sub>	Maximum Input Leakage Current	V <sub>IN</sub> = V <sub>CC</sub> or GND	6.0	± 0.1	±1.0	±1.0	μΑ
I <sub>OZ</sub>	Maximum Three–State Leakage Current	Output in High Impedance State $V_{IN} = V_{IL}$ or $V_{IH}$ $V_{OUT} = V_{CC}$ or GND	6.0	± 0.5	±5.0	±10.0	μΑ
I <sub>CC</sub>	Maximum Quiescent Supply Current (per Package)	$V_{IN} = V_{CC}$ or GND $I_{OUT} = 0 \mu A$	6.0	4	40	160	μΑ

<sup>9.</sup> Information on typical parametric values can be found in the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

### AC CHARACTERISTICS ( $C_L = 50 \text{ pF}$ , Input $t_r = t_f = 6 \text{ ns}$ )

		V <sub>CC</sub>	Guaran	Guaranteed Limit		
Symbol	Parameter	٧	-55°C to 25°C	≤ <b>85</b> ° <b>C</b>	≤125°C	Unit
t <sub>PLH</sub> ,	Maximum Propagation Delay, Input A to Output Y	2.0	80	100	120	ns
t <sub>PHL</sub>	(Figures 3 and 5)	3.0	30	40	55	
		4.5	18	23	28	
		6.0	15	20	25	
t <sub>PLZ</sub> ,	Maximum Propagation Delay, Output Enable to Output Y	2.0	110	140	165	ns
t <sub>PHZ</sub>	(Figures 4 and 6)	3.0	45	60	75	
	,	4.5	25	31	38	
		6.0	21	26	31	
t <sub>PZL</sub> ,	Maximum Propagation Delay, Output Enable to Output Y	2.0	110	140	165	ns
t <sub>PZH</sub>	(Figures 4 and 6)	3.0	45	60	75	
		4.5	25	31	38	
		6.0	21	26	31	
t <sub>TLH</sub> ,	Maximum Output Transition Time, Any Output	2.0	60	75	90	ns
t <sub>THL</sub>	(Figures 3 and 5)	3.0	22	28	34	
		4.5	12	15	18	
		6.0	10	13	15	
C <sub>IN</sub>	Maximum Input Capacitance		10	10	10	pF
C <sub>OUT</sub>	Maximum Three–State Output Capacitance (High Impedance State Output)		15	15	15	pF

<sup>10.</sup> For propagation delays with loads other than 50 pF, and information on typical parametric values, see the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, $V_{CC} = 5.0 \text{ V}$ , $V_{EE} = 0 \text{ V}$	
$C_{PD}$	Power Dissipation Capacitance (Per Buffer) (Note 11)	35	pF

<sup>11.</sup> Used to determine the no-load dynamic power consumption:  $P_D = C_{PD} \ V_{CC}^2 f + I_{CC} \ V_{CC}$ . For load considerations, see the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

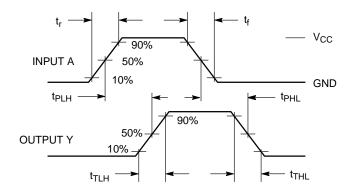


Figure 3. Switching Waveform

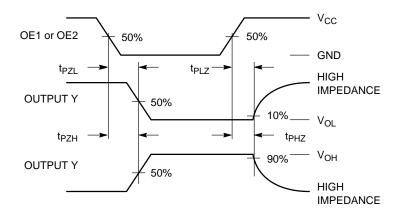
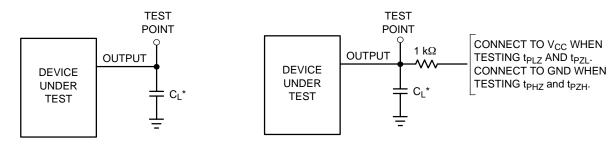


Figure 4. Switching Waveform

PIN DESCRIPTIONS



<sup>\*</sup>Includes all probe and jig capacitance

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Figure 5. Test Circuit

Figure 6. Test Circuit

### INPUTS

### A1, A2, A3, A4, A5, A6, A7, A8 (PINS 2, 3, 4, 5, 6, 7, 8, 9)

Data input pins. Data on these pins appear in non-inverted form on the corresponding Y outputs, when the outputs are enabled.

### **CONTROLS**

### OE1, OE2 (PINS 1, 19)

Output enables (active-low). When a low voltage is applied to both of these pins, the outputs are enabled and the

device functions as an non-inverting buffer. When a high voltage is applied to either input, the outputs assume the high impedance state.

### **OUTPUTS**

## Y1, Y2, Y3, Y4, Y5, Y6, Y7, Y8 (PINS 18, 17, 16, 15, 14, 13, 12, 11)

Device outputs. Depending upon the state of the output enable pins, these outputs are either non–inverting outputs or high–impedance outputs.

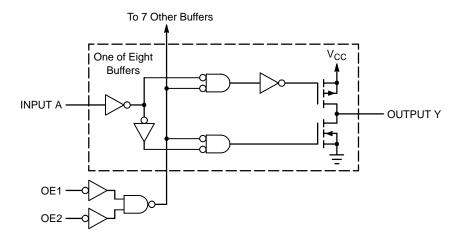
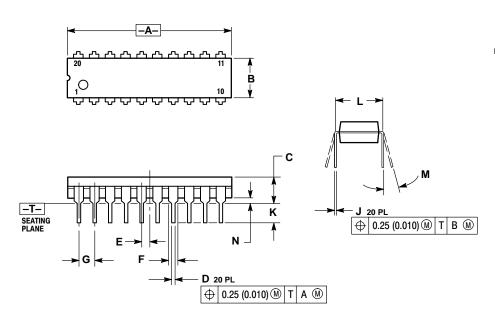


Figure 7. Logic Detail

### **PACKAGE DIMENSIONS**

### **PDIP N SUFFIX** PLASTIC DIP PACKAGE CASE 738-03 ISSUE E

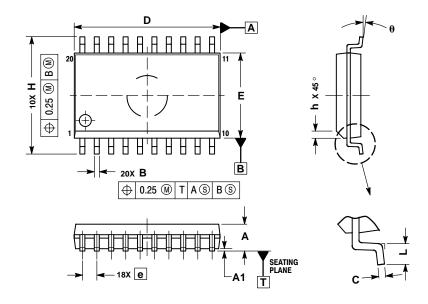


### NOTES:

- OLES:
  1. DIMENSIONING AND TOLERANCING PER ANSI
  Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. DIMENSION L TO CENTER OF LEAD WHEN
  FORMED PARALLEL.
  4. DIMENSION B DOES NOT INCLUDE MOLD
  ET ACH

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	1.010	1.070	25.66	27.17	
В	0.240	0.260	6.10	6.60	
С	0.150	0.180	3.81	4.57	
D	0.015	0.022	0.39	0.55	
Е	0.050	0.050 BSC		BSC	
F	0.050	0.070	1.27	1.77	
G	0.100	BSC	2.54	BSC	
J	0.008	0.015	0.21	0.38	
K	0.110	0.140	2.80	3.55	
L	0.300	BSC	7.62	BSC	
M	0°	15°	0°	15°	
N	0.020	0.040	0.51	1.01	

SO-20 **DW SUFFIX** CASE 751D-05 ISSUE F



### NOTES:

- NOTES:

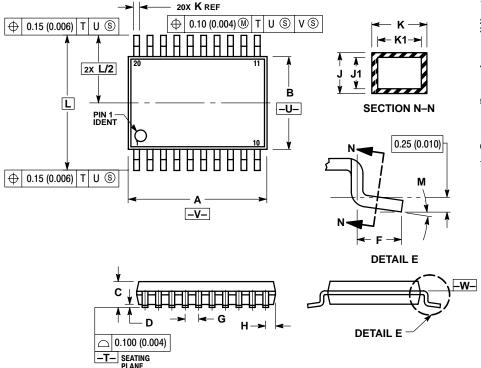
  1. DIMENSIONS ARE IN MILLIMETERS.
  2. INTERPRET DIMENSIONS AND TOLERANCES
  PER ASME Y14.5M, 1994.
  3. DIMENSIONS D AND E DO NOT INCLUDE MOLD
  PROTRUSION.
  4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
  5. DIMENSION B DOES NOT INCLUDE DAMBAR
  PROTRUSION. ALLOWABLE PROTRUSION SHALL
  BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT
  MAXIMUM MATERIAL CONDITION.

	l				
	MILLIMETERS				
DIM	MIN	MAX			
Α	2.35	2.65			
A1	0.10	0.25			
В	0.35	0.49			
С	0.23	0.32			
D	12.65	12.95			
Е	7.40	7.60			
е	1.27	BSC			
Н	10.05	10.55			
h	0.25	0.75			
L	0.50	0.90			
θ	0°	7 °			

### PACKAGE DIMENSIONS

### **TSSOP** DT SUFFIX

20 PIN PLASTIC TSSOP PACKAGE CASE 948E-02 **ISSUE A** 



- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- TH-3-MM, 1992...
  CONTROLLING DIMENSION: MILLIMETER.
  DIMENSION A DOES NOT INCLUDE MOLD FLASH,
  PROTRUSIONS OR GATE BURRS. MOLD FLASH
  OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
  DIMENSION B DOES NOT INCLUDE INTERLEAD
- FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

  DIMENSION K DOES NOT INCLUDE DAMBAR
- PROTRUSION. ALLOWABLE DAMBAR
  PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
- 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	6.40	6.60	0.252	0.260	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65 BSC		0.026	BSC	
Н	0.27	0.37	0.011	0.015	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
Ĺ	6.40		0.252 BSC		
M	0°	8°	0°	8°	

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